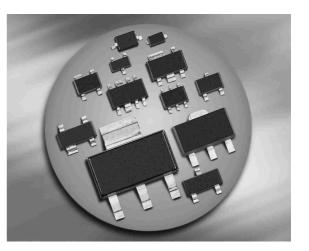


BBY65...

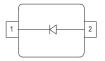
## Silicon Tuning Diode

- High Q hyperabrupt tuning diode
- Very low capacitance spread
- Designed for low tuning voltage operation for VCO's in mobile communications equipment
- For low frequency control elements such as TCXOS and VCXOS
- High capacitance ratio and good C-V linearity
- Pb-free (RoHS compliant) package





## BBY65-02V



Туре	Package	Configuration	L <sub>S</sub> (nH)	Marking
BBY65-02V	SC79	single	0.6	F

## **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V <sub>R</sub>	15	V	
Forward current	/ <sub>F</sub>	50	mA	
Operating temperature range	T <sub>op</sub>	-55 150	°C	
Storage temperature	T <sub>stg</sub>	-55 150		



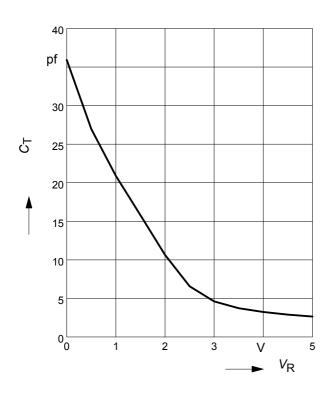
Parameter	Symbol		Values			
		min.	typ.	max.	1	
DC Characteristics	·		•		•	
Reverse current	I <sub>R</sub>				nA	
<i>V</i> <sub>R</sub> = 10 V		-	-	10		
$V_{\rm R}$ = 10 V, $T_{\rm A}$ = 85 °C		-	-	100		
AC Characteristics						
Diode capacitance	CT				pF	
<i>V</i> <sub>R</sub> = 0.3 V, <i>f</i> = 1 MHz		28.2	29.5	30.8		
V <sub>R</sub> = 1 V, <i>f</i> = 1 MHz		-	20.25	-		
<i>V</i> <sub>R</sub> = 2 V, <i>f</i> = 1 MHz		-	9.8	-		
<i>V</i> <sub>R</sub> = 3 V, <i>f</i> = 1 MHz		-	4.45	-		
$V_{\rm R}$ = 4.7 V, <i>f</i> = 1 MHz		2.6	2.7	2.8		
Capacitance ratio	C <sub>T0.3</sub> /	10	10.9	-	pF	
$V_{\rm R}$ = 0.3 V, $V_{\rm R}$ = 4.7 V	C <sub>T4.7</sub>					
Capacitance ratio	C <sub>T1</sub> /C <sub>T3</sub>	-	4.55	-	pF	
<i>V</i> <sub>R</sub> = 1 V, <i>V</i> <sub>R</sub> = 3 V						
Series resistance	r <sub>S</sub>	-	0.6	0.9	Ω	
V <sub>R</sub> = 1 V, <i>f</i> = 470 MHz						

## **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

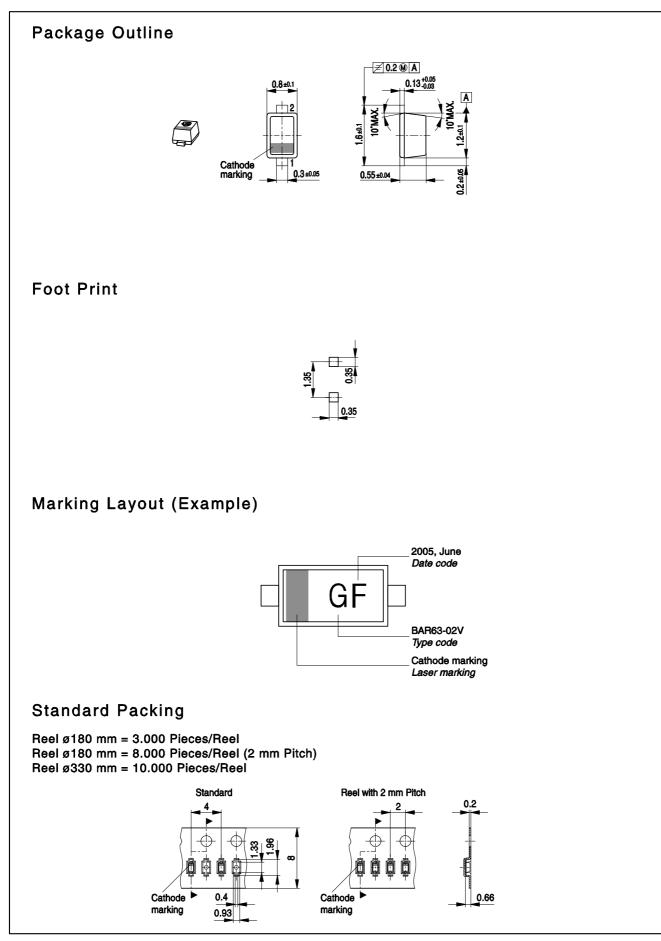


## **Diode capacitance** $C_{T} = f(V_{R})$

f = 1 MHz











# Date Code marking for discrete packages with one digit (SCD80, SC79, SC75<sup>1)</sup>) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	а	р	А	Ρ	а	р	А	Р	а	р	А	Р
02	b	q	В	Q	b	q	В	Q	b	q	В	Q
03	С	r	С	R	С	r	С	R	С	r	С	R
04	d	S	D	S	d	S	D	S	d	s	D	S
05	е	t	E	Т	е	t	E	Т	е	t	Е	Т
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	V	G	V	g	V	G	V	g	V	G	V
08	h	х	Н	Х	h	х	Н	Х	h	х	Н	Х
09	j	у	J	Y	j	у	J	Y	j	у	J	Y
10	k	Z	K	Z	k	Z	K	Z	k	Z	K	Z
11	I	2	L	4	I	2	L	4	I	2	L	4
12	n	3	Ν	5	n	3	Ν	5	n	3	Ν	5

1) New Marking Layout for SC75, implemented at October 2005.





Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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